## Interactions, disorder and local defects in graphite

M A H. Vozm ediano,<sup>1</sup> and F. Guinea<sup>2</sup>, and M. P. Lopez-Sancho<sup>2</sup>

 $^{\rm 1}$  D epartam ento de M atem aticas, U nidad A sociada C SIC -U C 3M ,

Universidad Carlos III de Madrid, E-28911 Leganes, Madrid, Spain.

<sup>2</sup> Instituto de Ciencia de Materiales de Madrid, CSIC, Cantoblanco, E-28049 Madrid, Spain.

(D ated: A pril 14, 2024)

Recent experiments report the existence of ferrom agnetic and superconducting uctuations in graphite at unexpectedly high temperatures. The interplay of disorder and interactions in a 2D graphene layer is shown to give rise to a rich phase diagram where strong coupling phases can become stable. Local defects can explain the ferrom agnetic signals.

PACS numbers: 75.10 Jm, 75.10 Lp, 75.30 Ds, 71.20 Tx, 73.50 Gr

Introduction. A number of recent experiments suggest that pure graphite behaves as a highly correlated electron system [1]. In particular it shows a metal-insulator transition in magnetic elds and insulating behavior in the direction perpendicular to the planes in di erent sam ples [2, 3, 4, 5, 6, 7, 8, 9]. The interest in this material is focussed now adays in the observation of ferrom agnetic behavior [10], enhanced by proton bom bardment [11] what opens a new way to the creation of organic magnets.

In refs.[12, 13] a simple m icroscopic model was proposed as a new fram ework to study the physics of 2D graphene sheets and its topological variant fullerenes and carbon nanotubes. The main assumption of the model is to neglect the coupling between layers and consider graphite as a pure two-dimensional system. This assumption is supported by experiments where an anisotropy of up to three orders of magnitude is measured in magnetotransport[5]. The model predicts non-Ferm i liquid behavior for the graphene system and can account for the linear behavior with energy of the quasiparticle scattering rate[14] observed in photoem ission experiments[15].

In this work we review the main features of the model with and without disorder and propose a new mechanism to explain the ferrom agnetic uctuations observed in the experiments.

The model. RG results. The conduction band of graphite is well described by tight binding models which include only the orbitals which are perpendicular to the graphite planes at each C atom [16]. The two dimensional hexagonal lattice of a graphene plane has two atom sper unit cell. A tight binding calculation with only nearest neighbors hopping gives rise to the dispersion relation

$$E (k) = t 1 + 4\cos^2 \frac{p_3}{2}k_x + 4\cos \frac{p_3}{2}k_x \cos \frac{3}{2}k_y (1)$$

whose lower branch is shown in Fig.1. This dispersion relation gives rise at half lling to a Ferm i surface consisting of six isolated points two of which are inequivalent. A low-energy e ective H am iltonian can be de ned by expanding the dispersion relation about any of the Ferm i points. The resulting H am iltonian has the form of a m assless two dimensional D irac H am iltonian. The

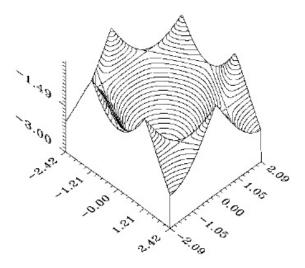


FIG.1: Lower branch of the electronic dispersion relation. The cusps appear at the six corners of the rst B rillouin zone.

Ferm i velocity,  $v_F$ , can be expressed in term s of the matrix elements between nearest neighbor orbitals, t, as  $v_F = (3ta)=2$ , where a is the C-C distance.

The electronic states within each graphene plane are described by two two-component spinors associated to the two inequivalent Ferm i points in the Brilbuin Zone. The Ham iltonian of the free system is:

$$H_{0} = iv_{F} \quad d^{2}x (x) \sim \tilde{r} (x)$$
 (2)

where the two-dimensional matrices are built as appropriate combinations of Paulimatrices [12]. The Ham iltonian (2) gives an elective description of graphite in an energy range bound by a lower cuto 27eV dictated by the interlayer coupling, and a higher cuto , where the bands can no longer be approximated by a linear dispersion relation 3 4eV.

The Ham iltonian (2) is the perfect model for Renormalization G roup (RG) calculations. It is scale invariant and does not have the complications of an extended Ferm isurface. The model is similar to the D = 1 electron system in that it has Ferm ipoints and linear dispersion. N evertheless naive dimensional analysis shows that four and more Ferm i interactions are irrelevant in this twodimensional case. The only interaction that may survive at low energies is the long (in nite) range Coulomb interaction, unscreened because of the vanishing density of states at the Ferm i point. Following the quantum eld theory nature of the model, we trade the classical Coulomb interaction

$$H_{ee} = \frac{V_F}{4} \begin{bmatrix} 2 \\ d^2 x d^2 x^{(-)}(x) \\ d^2 x d^2 x^{(-)}(x) \end{bmatrix} (x^{-}) \frac{g}{jx} \begin{bmatrix} x^{-0} \\ x^{-1} \end{bmatrix} (x^{-})$$
(3)

where  $g = e^2=4 v_F$  is the dimensionless coupling constant, by a local gauge interaction through a minimal coupling.

$$L_{int} = g d^{2}xdtj (x;t)A (x;t); \qquad (4)$$

where the electron current is de ned as

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$$j = (0; v_F)^{-1}$$
;  $v_F$   $i$ ):

This interaction is marginal in the RG sense, all the rest are irrelevant. The RG analysis of the model gives the following results [12, 13]:

1. From the computation of the electron self-energy at the one loop level we get a non trivial renorm alization of the Ferm i velocity that grow s in the infrared. This result im plies a breakdown of the relation between the energy and momentum scaling, a signature of a quantum critical point.

2. The electron-photon vertex and the photon propagator are not renorm alized at the one loop level. This means that the electric charge is not renorm alized, a result that could be predicted by gauge invariance, and it also implies that the electric coupling constant  $g = e^2 = 4 v_F$  decreases at low energies de ning an infrared free xed point of the RG. It is interesting to note that the Lorentz invariance of the model that was explicitly broken by the Ferm i velocity is recovered at the xed point since the velocity of light, c, xes a limit to the growing of the Ferm i velocity.

2. From the electron self-energy at two loops order we get a non trivial wave function renormalization meaning that the infrared stable xed point corresponds to a free xed point di erent from the Ferm i liquid. This result has been shown to persist in the non-perturbative regime [17]. This is a non-trivial result that has physical implications. In particular it is plies that the inverse quasiparticle lifetime increases linearly with energy [14], a result that has been observed experimentally in [15] in the energy range of validity of the model.

In conclusion, we have shown that without disorder, edges, or other perturbations, the graphene system at low energies has gapless excitations di ering from the Ferm i liquid quasiparticles but does not support m agnetic or superconducting instabilities.

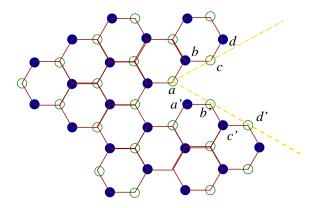


FIG. 2: Form ation of a pentagonal ring in the honeycomb lattice. Points a;b;c;d::: have to be identified with points  $a^0;b^0;c^0;d^0:::$ . The defect can be seen as a disclination, de ned by the straight dashed lines.

The strong coupling regime of the graphene system has been analyzed in [18, 19]. There it is argued that a dynam ical breakdown of the chiral symmetry (degeneracy between the two Ferm i points) will occur at strong coupling and a gap will open in the spectrum forming a kind of charge density wave. G raphite can then be seen as an excitonic insulator that can become ferrom agnetic upon doping. Being non-perturbative, these phenomena are likely to be washed out by any amount of disorder at intermediate energies.

## Inclusion of disorder.

The previous description analyzes the small momentum scattering due to the long range C oulomb interaction, as it is the only one which leads to logarithm ically divergent perturbative corrections. Some electronic instabilities, like ferrom agnetism or an isotropic superconductivity, require the existence of short range interactions with signi cant strength. The irrelevant character of short range interactions can be changed by the presence of disorder that enhances the density of states at the Ferm i level.

D isorder can be included in the renorm alization group scheme by the introduction of random gauge elds. This is a standard procedure in the study of the states described by the two dimensional D irac equation associated to random lattices or to integer quantum H all transitions [20, 21, 22]. There it is seen that, usually, the density of states at low energies is increased. To dem onstrate how these gauge elds can arise in the graphene system, we will describe in detail a special type of disorder that we call topological disorder.

The form ation of pentagons and heptagons in the lattice, without a ecting the threefold coordination of the carbon atom s, lead to the warping of the graphene sheets, and are responsible for the form ation of curved fullerenes, like  $C_{60}$ . They can be viewed as disclinations in the lattice, and, when circling one such defect, the two sublattices in the honeycom b structure are exchanged (see Fig.[2]). The two ferm ion avors associated to the two Ferm i points are also exchanged when moving around such a defect. The scheme to incorporate this change in a continuum description was discussed in [17]. The process can be described by means of a non Abelian gauge ekd, which rotates the spinors in avor space. The vector potential is that of a vortex at the position of the defect, and the ux is =2.

D islocations can be analyzed in term s of bound disclinations, that is, a pentagon and an heptagon located at short distances, which de ne the Burgers vector of the dislocation. Thus, the e ect of a dislocation on the electronic levels of a graphene sheet is analogous to that of the vector potential arising from a vortex-antivortex pair. W e can extend this description [23], and assume that a lattice distortion which rotates the lattice axis can be param etrized by the angle of rotation, (r), of the local axes with respect to a xed reference fram e. Then, this distortion induces a gauge eld such that:

$$A^{\prime}(\mathbf{r}) = 3\mathbf{r} \quad \mathbf{r} \quad$$

Thus, a random distribution of topological defects can be described by a (non abelian) random gauge eld.

O ther types of disorder can similarly be associated to random gauge elds. The complete Hamiltonian of the system can be written as

$$H = H_{ee} + H_{disorder}$$
 (6)

where

$$H_{ee} = \frac{V_F}{4} \begin{bmatrix} Z \\ d^2 x d^2 x^{(-)}(x) \\ 0 \end{bmatrix} (x) \frac{g}{jx} \frac{g}{x^0 j} (x^0) = (x^0)$$
(7)

$$H_{disorder} = \frac{v}{4} d^2 \mathbf{x} (\mathbf{x}) (\mathbf{x}) \mathbf{A} (\mathbf{x})$$
(8)

v characterizes the strength and the 4  $\,$  4 m atrix the type of the vertex. In general, A (x) is a quenched, G aussian variable with the dimensionless variance , i.e.,

hA (x) 
$$i = 0$$
; hA (x) A (x<sup>0</sup>)  $i = {}^{2}$  (x x<sup>0</sup>) : (9)

In ref. [24] a complete RG study of the disordered system was analyzed by adding gauge couplings associated to all possible gamma matrices. i) For a random chemical potential, the 4 4 m atrix is given by = 0. The long range components of this type of disorder do not induce transitions between the two inequivalent Fermi points. This type of disorder yields an unstable xed line. ii) A random gauge potential involves the 4 4 matrices =  $i_1$  and =  $i_2$ . This type of disorder gives rise to a stable xed line which is linear in the (q; )plane. iii) (a) A uctuating mass term is described by =  $1_{44}$ . (b) Topological disorder is given by =  $1_{5}$  $with_5 = 1_{22}$  $_2$ . c) To complete the discussion, we also mention =  $i_{5}$  where  $-5 = 1_{22}$  1. This vertex

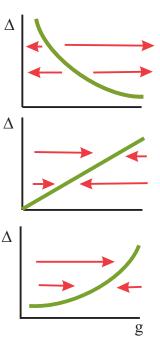


FIG. 3: O ne-loop phase diagram for two-dimensional massless D irac spinors including long-ranged electron-electron interaction g and disorder . Top: R andom chemical potential ( $= _0$ ). C enter: R andom gauge potential ( $= i_1; i_2$ ). Bottom: R andom m ass term ( $= 1_4_4$ ), topological disorder ( $= i_5$ ), and  $= i_{5}$ .

type can be related to an imaginary mass that couples the two inequivalent Ferm i points. All these types of disorder will yield a stable xed line which is cubic in the (g; )-plane.

The phase diagram obtained in [24] is reproduced in Fig. 3.

i) For a random chemical potential ( =  $_0$ ), v = v1 rem ains constant under renorm alization group transformation. There is an unstable xed line at  $v_F$  =  $v_1^2 = (2e^2)$ . In the (g; )-plane, the strong-coupling and the weak-coupling phases are separated by a hyperbola, with the critical electron interaction  $g = e^2 = v_F =$  $2e^4 = (v_1^2)$ . ii) A random gauge potential involves the vertices =  $i_1; i_2$ . The vertex strength renorm alizes as  $v~=~v_{\rm F}$  . There is thus an attractive Luttingerlike xed point for each disorder correlation strength given by  $v_F = 2e^2 = \text{ or } g = -2.$  iii) For a random mass term =  $1_{44}$ , topological disorder =  $i_{5}$ , and =  $i_{5}$ , we have  $v = v_F^2 = v_3$ . There is thus again an attractive Luttinger-like xed point for <u>each dis</u>order correlation strength given by  $v_F = \frac{1}{3} 2v_3^2 e^2 = or$  $q = \frac{r_3}{e^4 = (2v_3^2)}$ .

The most interesting phase is the one induced by a random gauge potential, a random mass term or the topological disorder. All of them drive the system towards a new stable, Luttinger-like xed point. This phase is characterized by a vanishing quasiparticle residue, leading to anom alous one particle properties. The Luttinger liquid features associated to this xed line are notoriously di cult to observe, although they can be probed in tunneling experiments, or by measuring the peak width in ARPES.They will also in uence the interlayer transport properties [25, 26]. Sm all perturbations by other types of disorder, like a random local potential induce a ow along this xed line, as in the absence of interactions [27]. The strong coupling xed point describes, most likely, a disordered insulating system.

Localized states. In addition to the extended disorder discussed previously, a graphene plane can show states bcalized at interfaces [28, 29], which, in the absence of other types of disorder, lie at the Ferm ienergy. Changes in the local coordination can also lead to localized states [30].

The tight binding model de ned by the orbitals at the lattice sites can have edge states when the sites at the edge belong all to the sam e sublattice (zig-zag edges) [28, 29]. These states lie at zero energy, which, for neutral graphene planes, correspond to the Ferm i energy.

In a strongly disordered sam ple, large defects m ade up of m any vacancies can exist. These defects give rise to localized states, when the term ination at the edges is locally sim ilar to the surfaces discussed above[31]. Note that, if the bonds at the edges are saturated by bonding to other elem ents, like hydrogen, the states at these sites are removed from the Ferm i energy, but a sim ilar boundary problem arises for the remaining orbitals. A particular sim ple exam ple is given by the crack shown in Fig.[4].

These states are half led in a neutral graphene plane. In the absence of electron interactions, this leads to a large degeneracy in the ground state. A nite local repulsion will tend to induce a ferrom agnetic alignm ent of the electrons occupying these states, as in sim ilar cases with degenerate bands[32]. Hence, we can assume that the presence of these states leads to magnetic mom ents localized near the defects.

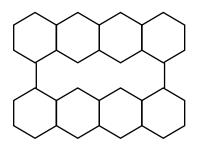


FIG.4: Example of a crack in a graphene plane. The atom s at the upper edge and those at the low er edge belong to di erent sublattices.

We now have to analyze the in uence of these magnetic m om ents in conduction band described in the previous sections. The hopping between the states involved in the form ation of these m om ents and the delocalized states in the conduction band vanishes by de nition, if the localized states lie at zero energy. Hence, a Kondo like coupling mediated by the hopping will not be induced. The localized and conduction band states, on the other hand, are de ned on the same lattice sites. The existence of a nite local repulsion, U, will lead to an e ective ferrom agnetic coupling. The local coupling, at site i, between the localized states and the conduction  $_{j}$   $_{i;j}$ , where  $_{i;j}$  is charge of band is proportional to U state j at site i. In order to get an order of m agnitude estim ate of the e ect of these states, we will assume that the num ber of states induced near a vacancy is sim ilar to the num ber of atom s at its edge, N , and that these states are su ciently localized around the vacancy. Hence, each vacancy nucleates a moment of order N . The e ective coupling between a vacancy and the conduction electrons is proportional to UN, and it is distributed over an area

N $^2$ . The conduction electrons will mediate an RKKY interaction between the localized moments:

$$J_{RKKY}(\mathbf{r}) U^2 d^2 k e^{i\mathbf{k}\cdot\mathbf{r}} (\mathbf{\tilde{k}}) U^2 \frac{a^4}{v_F \mathbf{j}^2 \mathbf{j}^3}$$
 (10)

W here the static susceptibility is (K) / JK j[14], and a is the lattice constant. It is interesting to note that, due to the absence of a nite Ferm i surface, the RKKY interaction in eq.(10) does not have oscillations. Hence, there are no competing ferro-and antiferrom agnetic couplings, and the m agnetic m om ents will tend to be ferrom agnetically aligned, leading to an elective m agnetic eld, H<sub>ext</sub> (r), with non zero average, acting on the conducting electrons.

From power counting, this coupling is relevant in the R enorm alization G roup sense. Thus, in the presence of extended vacancies, the RG ow discussed in the previous sections has to be arrested at scales comparable to  $hH_{ext}(\mathbf{r})i$  UN  $_{vac}$ , where  $_{vac}$  is the concentration of the large vacancies which m ay give rise to localized states. At low er energies, or tem peratures, the graphene planes with extended vacancies will behave as a ferrom agnet.

Conclusions. In this work we present a microscopic model for studying the low energy properties of a single graphene layer as a model relevant for som e graphite sam ples showing two-dimensional anom alous behavior. In particular we tried to envisage a model able to explain the ferrom agnetism observed recently in a variety of graphitic materials.

The model is based on the particular dispersion relation of the 2D honeycomb lattice that, at half lling, has Ferm i points instead of Ferm i lines. The linearization of the dispersion about a Ferm i point gives rise to a model sim ilar to the one-dimensional electron system with zero density of states at the Ferm i level. Unlike the 1D case, the real two-dimensional nature of the present model makes the four Ferm i interactions irrelevant in the renorm alization group sense while the long range C oulomb interaction is unscreened and plays an important role. It renorm alizes the Ferm i velocity that grows a thow energies while the elective charge is not renorm alized, a consequence of the gauge invariance. The elective coupling constant  $e^2 = v_F$  goes to zero driving the system to a non-trivial infrared free xed point. As a consequence of the singular C oulom b interaction, the electron acquires anom alous dimension and the quasiparticle scattering rate grows linearly with frequency at interm ediate frequencies, as observed in experiments. The model does not support m agnetic or any other short range interactions at this level.

The presence of disorder changes the previous situation in various respects. We have considered two types of disorder, non-local disorder as the one produced by in purities or lattice distortions, modelled by the coupling of the electrons to random gauge elds as in the random lattice models, and local large defects as the ones produced in the experiments by proton bom bardment. Extended disorder gives rise to a rich phase diagram with strong coupled phases whose physical properties are still to be analyzed. Local defects give rise to the appearance of local moments whose interaction can induce ferrom agnetism in large portion of the sample.

W e thank P.E squinazi for sharing his experim ents with us and for m any illum inating discussions. Funding from M CyT (Spain) through grant M AT 2002-0495-C 02-01 is acknow ledged.

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